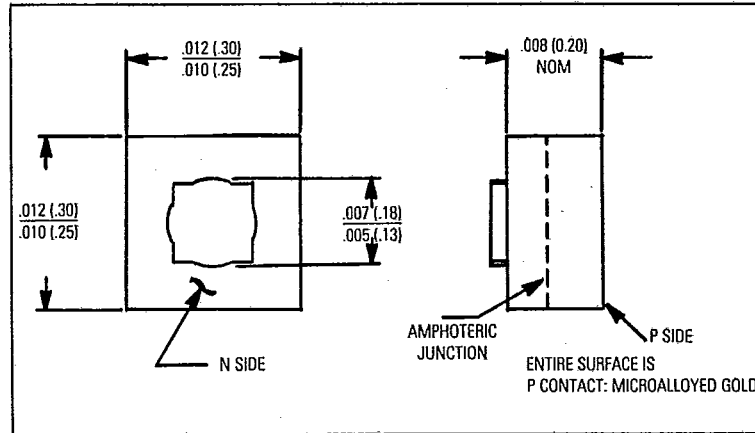
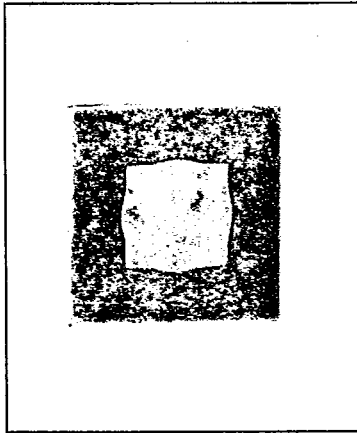




GaAlAs Infrared Emitter Chip Type OPC225

T-41-19



Features

- High Infrared radiation output
- Low degradation
- Microalloyed gold contacts

Description

Infrared emitting diode chips are fabricated by solution epitaxial techniques which provide high efficiency, long operating life, and minimum degradation. Spectral emission is centered at 890 nanometers.

Since Optek has no control over the techniques the customer may use to alloy and bond chips, Optek cannot be held responsible for damage to the chips resulting from such techniques. Nor can Optek warrant the life or any other parameter after the chips have been bonded.

Packaging Options

- OPC225 Vials
- OPC225TP Sawn on Tape
- OPC225WP Waffle Pack

Replaces

OPC230

Absolute Maximum Ratings ⁽¹⁾(T_A = 25°C unless otherwise noted)

Storage and Operating Temperature	-55°C to +150°C
Forward DC Current	150mA ⁽²⁾
Peak Forward Current (1 μs pulse width, 300 pps)	3.0A
Power Dissipation	200mW

Electrical Characteristics (T_A = 25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
V _R	Reverse Voltage	2.0			V	I _R = 10μA
V _F	Forward Voltage		1.95		V	I _F = 100mA
P _O	Radiant Power Output	4.0	7.5		mW	I _F = 100mA ⁽³⁾

Notes: (1) All maximum ratings are determined with the chip mounted on a dimpled TO-46 header using Optek techniques. (2) Maximum operating current is a function of the package in which the chip is housed and the environment in which the assembled package will be used. (3) Typical wavelength at peak emission is 890 nm.